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Douglas J. Resnick
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Lloyd C. Litt, SEMATECH Inc. (United States) and GLOBALFOUNDRIES Inc. (United States)
Hans Loeschner, IMS Nanofabrication AG (Austria)
John G. Maltabes, Hewlett-Packard Laboratories (United States)
Osamu Nagarekawa, HOYA Corporation (Japan)
Laurent Pain, Laboratory d'Electronique de Technologie de l'Information (France)
Ivo W. Rangelow, Technische Universität Ilmenau (Germany)
Benjamen M. Rathsack, Tokyo Electron America, Inc. (United States)
Ricardo Ruiz, Hitachi Global Storage Technologies, Inc. (United States)
Frank M. Schellenberg, Consultant (United States)

Ines A. Stolberg, Vistec Electron Beam Lithography Group (Germany)
Kevin T. Turner, University of Pennsylvania (United States)
James J. Watkins, University of Massachusetts Amherst (United States)
Wei Wu, Hewlett-Packard Laboratories (United States)

Session Chairs

1 Keynote Session
William M. Tong, KLA-Tencor Corporation (United States)
Douglas J. Resnick, Molecular Imprints, Inc. (United States)

2 Imprint I: Processing
John G. Maltabes, Hewlett-Packard Laboratories (United States)
Tatsuhiko Higashiki, Toshiba Corporation (Japan)

3 Directed Self-Assembly I: Resist Processing: Joint Session with Conference 8325
Frank M. Schellenberg, Consultant (United States)

4 Maskless/Direct-Write Lithography I
Hans Loeschner, IMS Nanofabrication AG (Austria)
Shy-Jay Lin, Taiwan Semiconductor Manufacturing Company Ltd. (Taiwan)

5 Modeling of Alternative Lithographic Processes
Frank M. Schellenberg, Consultant (United States)
Ines A. Stolberg, Vistec Electron Beam Lithography Group (Germany)

6 Metrology and Inspection for Alternative Lithographic Technologies: Joint Session with Conference 8324
Joy Y. Cheng, IBM Almaden Research Center (United States)
Martha I. Sanchez, IBM Almaden Research Center (United States)

7 Hybrid Directed Self-Assembly and Imprint Processes (DSA II and Imprint II)
Douglas J. Resnick, Molecular Imprints, Inc. (United States)
Christopher Bencher, Applied Materials, Inc. (United States)

8 Directed Self-Assembly III: Patterning
Benjamen M. Rathsack, Tokyo Electron America, Inc. (United States)
Joy Y. Cheng, IBM Almaden Research Center (United States)

9 Maskless/Direct-Write Lithography II
Marco Wieland, MAPPER Lithography (Netherlands)
Cynthia Hanson, Space and Naval Warfare Systems Center Pacific (United States)

10 Imprint III: Templates, Masks, and Molds
Wei Wu, Hewlett-Packard Laboratories (United States)
James A. Liddle, National Institute of Standards and Technology (United States)

11 Frontier Lithographic Techniques and Applications
Lloyd C. Litt, SEMATECH North (United States)
Hans Loeschner, IMS Nanofabrication AG (Austria)

12 Imprint IV: R2R Imprint Lithography and Applications
John G. Maltabes, Hewlett-Packard Laboratories (United States)
Ivo W. Rangelow, Technische Universität Ilmenau (Germany)

13 Directed Self-Assembly IV: Materials for Fine Process Control
Ricardo Ruiz, Hitachi Global Storage Technologies, Inc. (United States)
Elizabeth A. Dobisz, Hitachi Global Storage Technologies, Inc. (United States)